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SERIAL NUMBER 10/681,346	FILING DATE 10/09/2003  RULE	CLASS 438	GROUP ART UNIT 2818	ATTORNEY DOCKET NO. 249/286 DIV.
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APPLICANTS

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\*\* CONTINUING DATA \*\*\*\*\*

This application is a DIV of 10/125,597 04/19/2002 PAT 6,670,670 yes

\*\* FOREIGN APPLICATIONS \*\*\*\*\*

REPUBLIC OF KOREA 2001-25569 05/10/2001 yes

IF REQUIRED, FOREIGN FILING LICENSE GRANTED

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Foreign Priority claimed <input checked="" type="checkbox"/> yes <input type="checkbox"/> no	STATE OR COUNTRY KOREA, REPUBLIC OF	SHEETS DRAWING 8	TOTAL CLAIMS 30	INDEPENDENT CLAIMS 3
35 USC 119 (a-d) conditions met <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance				
Verified and Acknowledged Examiner's Signature _____ Initials _____				

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TITLE

Method for manufacturing a single electron memory device having quantum dots between gate electrode and single electron storage element